

IN THE CLAIMS:

Please substitute the following claims for the same-numbered claims in the application:

1. (Canceled).
2. (Currently Amended) The structure in claim [[1]] 7, wherein said hardmask is located along the top and sides of said upper capacitor plate.
3. (Currently Amended) The structure in claim [[1]] 7, wherein said hardmask has a pattern matching an etched pattern within said lower conductor layer.
4. (Currently Amended) The structure in claim [[1]] 7, wherein said lower capacitor plate, said capacitor dielectric, and said upper capacitor plate comprise a metal-insulator-metal capacitor.
5. (Original) The structure in claim 4, wherein said metal-insulator-metal capacitor comprises a single metal-insulator-metal capacitor, wherein said structure further comprises at least one dual metal-insulator-metal capacitor, and wherein said dual metal-insulator-metal capacitor includes a second capacitor dielectric and a second upper plate.
6. (Currently Amended) The structure in claim [[1]] 7, further comprising an insulator layer covering said hardmask, wherein said hardmask is distinct from said insulator layer.
7. (Currently Amended) A metal-insulator-metal capacitor structure comprising:
a lower conductor layer, wherein said lower conductor layer includes a least one lower capacitor plate and at least one wiring pattern;
at least one capacitor dielectric above said lower capacitor plate;

at least one upper capacitor plate above said capacitor dielectric; and
a hardmask above said upper capacitor plate,

The structure in claim 1, wherein spacing between wires in said wiring pattern is approximately one-third the height of said upper capacitor plate above the bottom of said lower capacitor plate.

8. (Canceled).

9. (Currently Amended) The structure in claim [[8]] 14, wherein said etch stop layer is located along the top and sides of said upper capacitor plate.

10. (Currently Amended) The structure in claim [[8]] 14, wherein said hardmask has a pattern matching an etched pattern within said lower conductor layer.

11. (Currently Amended) The structure in claim [[8]] 14, wherein said lower capacitor plate, said capacitor dielectric, and said upper capacitor plate comprise a metal-insulator-metal capacitor.

12. (Original) The structure in claim 11, wherein said metal-insulator-metal capacitor comprises a single metal-insulator-metal capacitor, wherein said structure further comprises at least one dual metal-insulator-metal capacitor, and wherein said dual metal-insulator-metal capacitor includes a second capacitor dielectric and a second upper plate.

13. (Currently Amended) The structure in claim [[8]] 14, further comprising an insulator layer covering said hardmask, wherein said hardmask is distinct from said insulator layer.

14. (Currently Amended) A metal-insulator-metal capacitor structure comprising:
a lower conductor layer, wherein said lower conductor layer includes at least one lower
capacitor plate and at least one wiring pattern;

at least one capacitor dielectric above said lower capacitor plate;
at least one upper capacitor plate above said capacitor dielectric;
an etch stop layer on said upper capacitor plate; and
a hardmask on said etch stop layer,

~~The structure in claim 8,~~ wherein spacing between wires in said wiring pattern is approximately one-third the height of said upper capacitor plate above the bottom of said lower capacitor plate.

15-28. (Canceled).